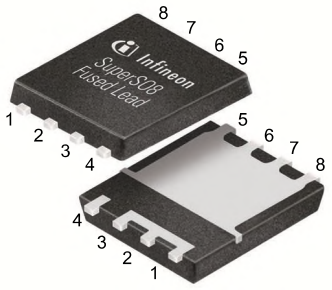
MOSFET

OptiMOS™ Power-MOSFET, 30 V

TDSON-8 FL (enlarged source interconnection)



Features

- Optimized for high performance Buck converter
- 175 °C rated
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

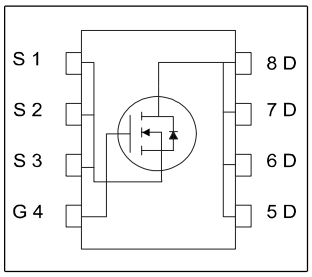


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on),max}$	1.1	mΩ
I_D	240	A
Q_{OSS}	40	nC
Q_G(0V..10V)	72	nC

Type / Ordering Code	Package	Marking	Related Links
BSC011N03LST	PG-TDSON-8 FL	011N03LT	-

[1] J-STD20 and JESD22

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - - -	- - - - -	240 170 213 150 39	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=4.5 V, T_C=25 °C V_{GS}=4.5 V, T_C=100 °C V_{GS}=10 V, T_A=25 °C, R_{thJA}=50 K/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	960	A	T_C=25 °C
Avalanche current, single pulse[4]	I_{AS}	-	-	50	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	190	mJ	I_D=50 A, R_{GS}=25 Ω
Gate source voltage[5]	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	115 3.0	W	T_C=25 °C T_A=25 °C, R_{thJA}=50 K/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	1.3	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm^2 cooling area[2]	R_{thJA}	-	-	50	K/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information
[5] The negative rating is for low duty cycle pulse occurrence. No continuous rating is implied

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	1.2	-	2	V	V_{DS}=V_{GS}, I_D=250 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=30 V, V_{GS}=0 V, T_j=25 °C V_{DS}=30 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	1.1 0.9	1.4 1.1	mΩ	V_{GS}=4.5 V, I_D=30 A V_{GS}=10 V, I_D=30 A
Gate resistance[1)]	R_G	0.3	0.6	1.2	Ω	-
Transconductance	g_{fs}	85	170	-	S	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=30 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	4700	6300	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	1500	2000	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	220	-	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	6.7	-	ns	V_{DD}=15 V, V_{GS}=10 V, I_D=30 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	8.8	-	ns	V_{DD}=15 V, V_{GS}=10 V, I_D=30 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	37	-	ns	V_{DD}=15 V, V_{GS}=10 V, I_D=30 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	6.2	-	ns	V_{DD}=15 V, V_{GS}=10 V, I_D=30 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge[1)]	Q_{gs}	-	11	15	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Gate charge at threshold	$Q_{g(th)}$	-	7.5	-	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Gate to drain charge[1)]	Q_{gd}	-	10.3	13	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Switching charge	Q_{sw}	-	14	-	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	36	48	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Gate plateau voltage	$V_{plateau}$	-	2.4	-	V	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	72	96	nC	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	29	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 4.5 V
Output charge[1)]	Q_{oss}	-	40	53	nC	V_{DD}=15 V, V_{GS}=0 V

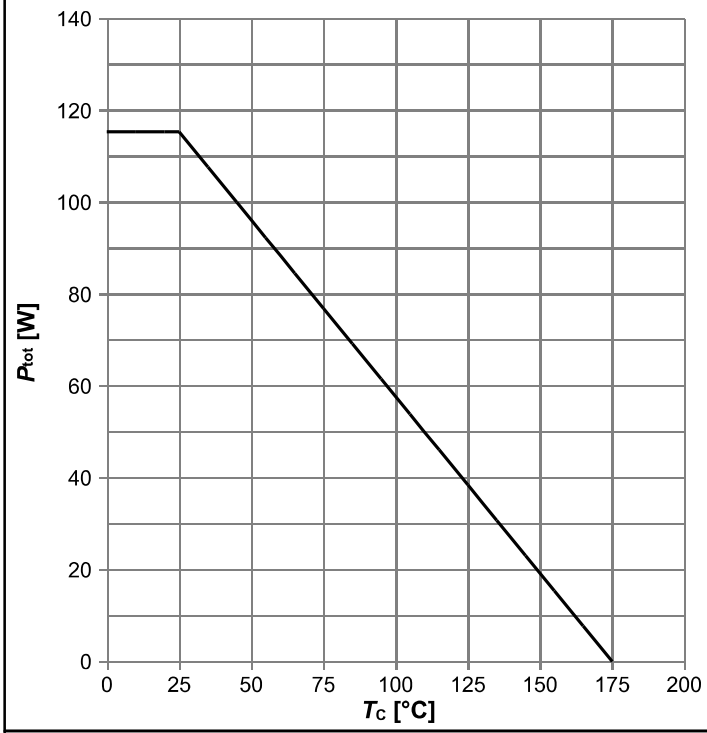
[1)] Defined by design. Not subject to production test
[2)] See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	115	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	960	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.8	1	V	V_{GS}=0 V, I_F=30 A, T_j=25 °C
Reverse recovery charge	Q_{rr}	-	20	-	nC	V_R=15 V, I_F=I_S, di_F/dt=400 A/µs

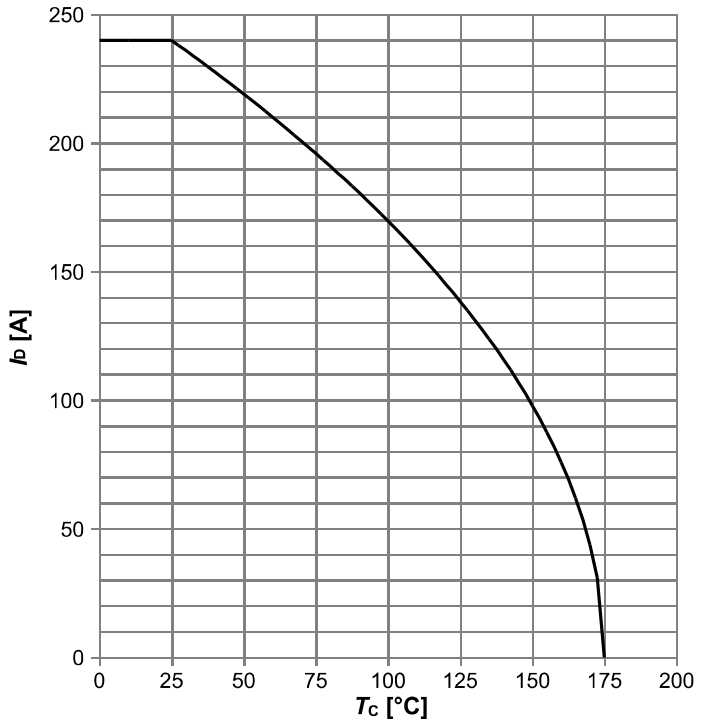
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



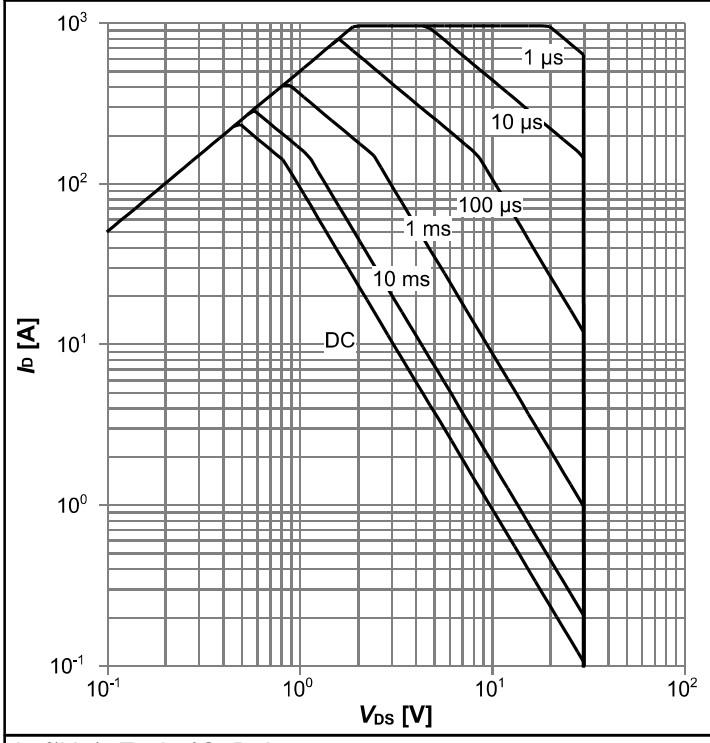
$P_{tot}=f(T_C)$

Diagram 2: Drain current



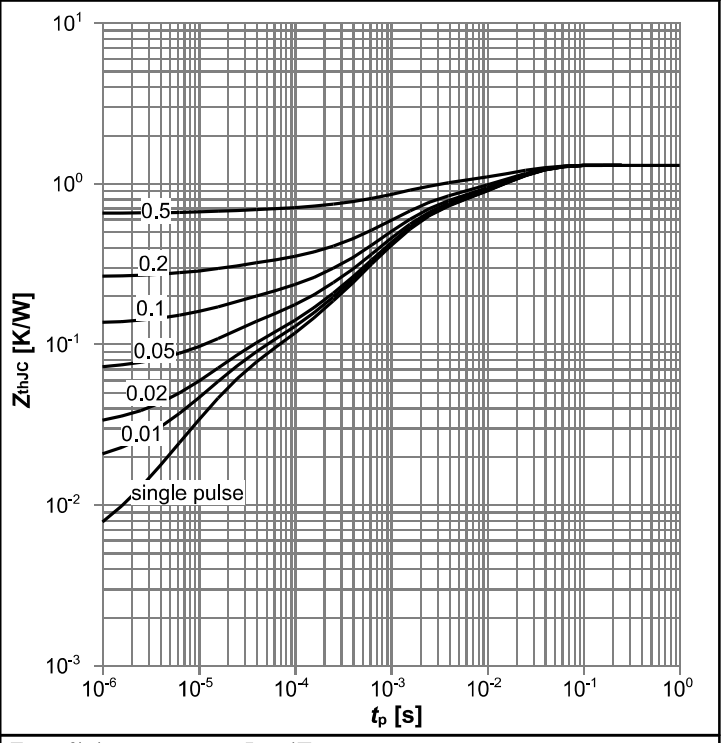
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



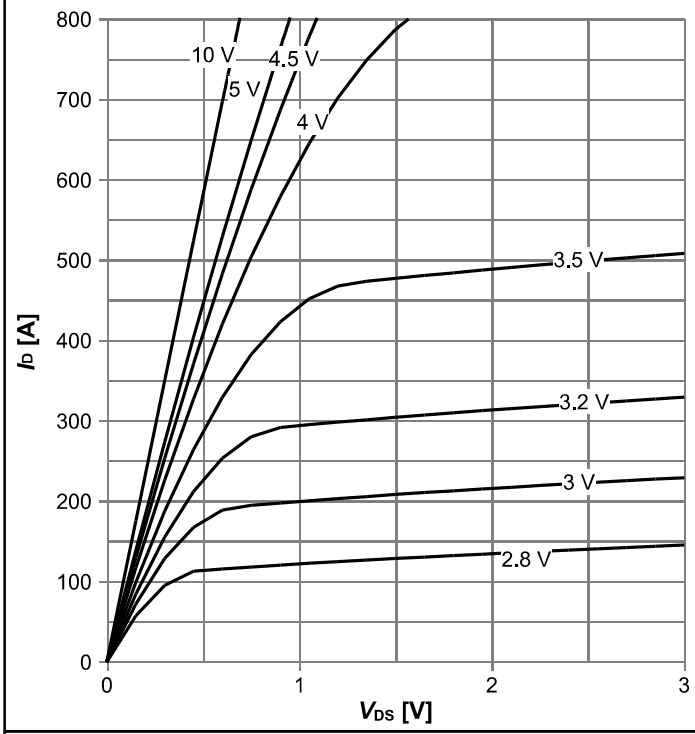
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



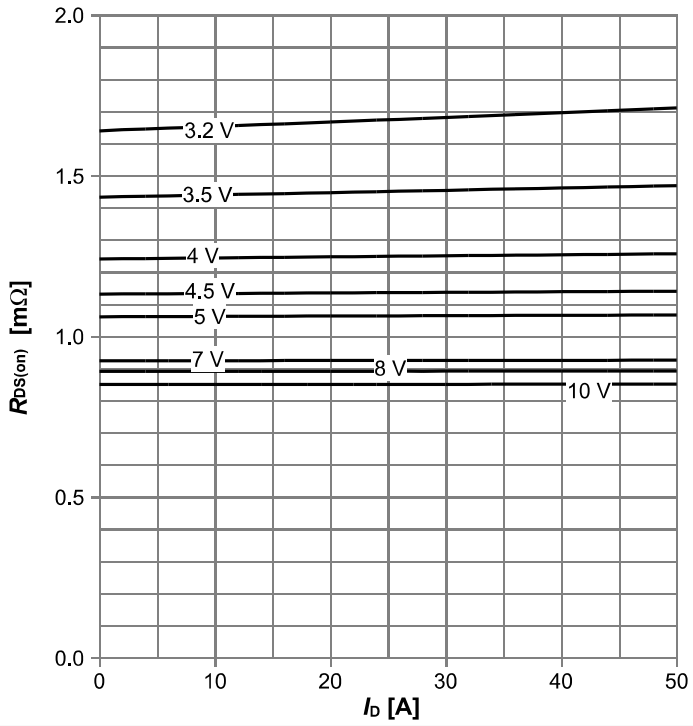
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



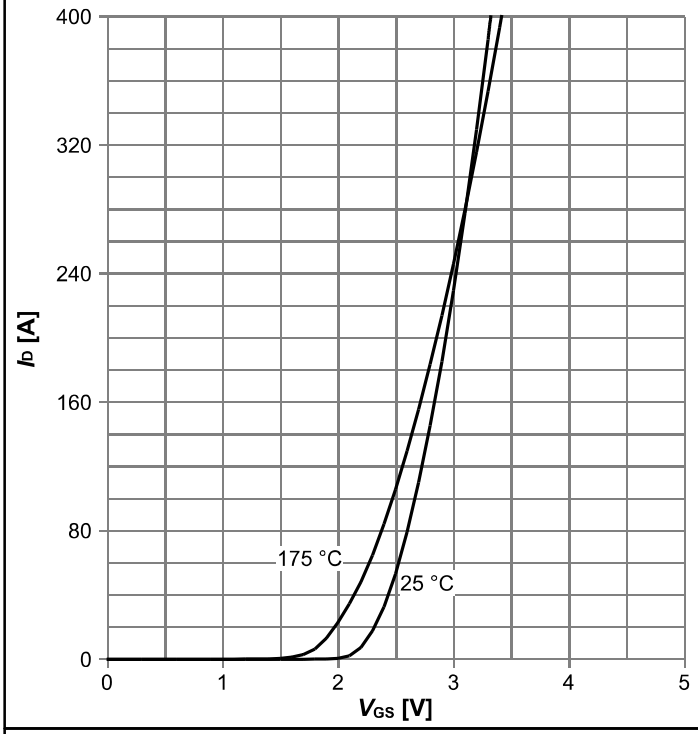
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



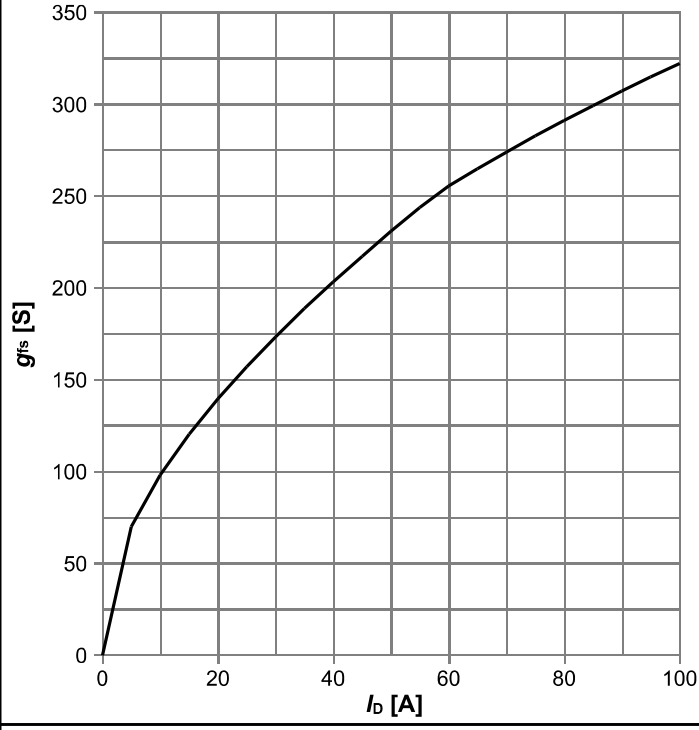
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



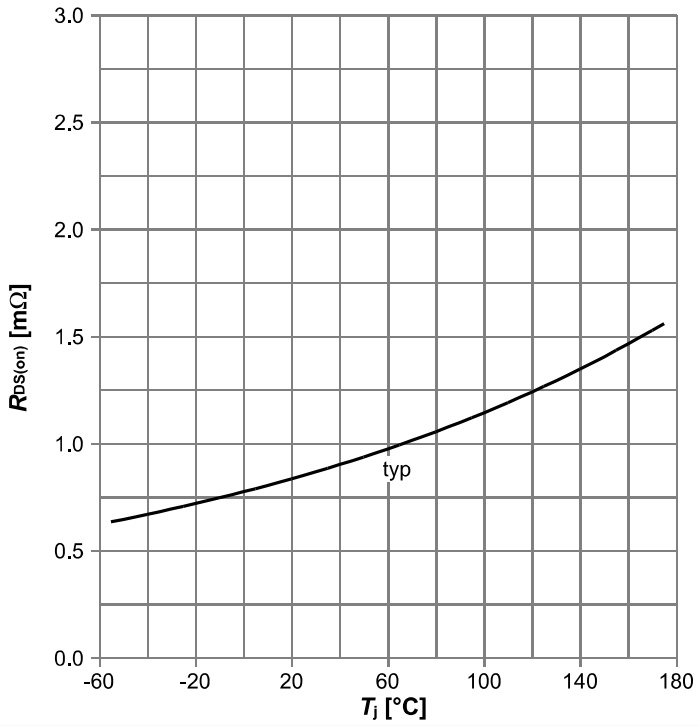
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



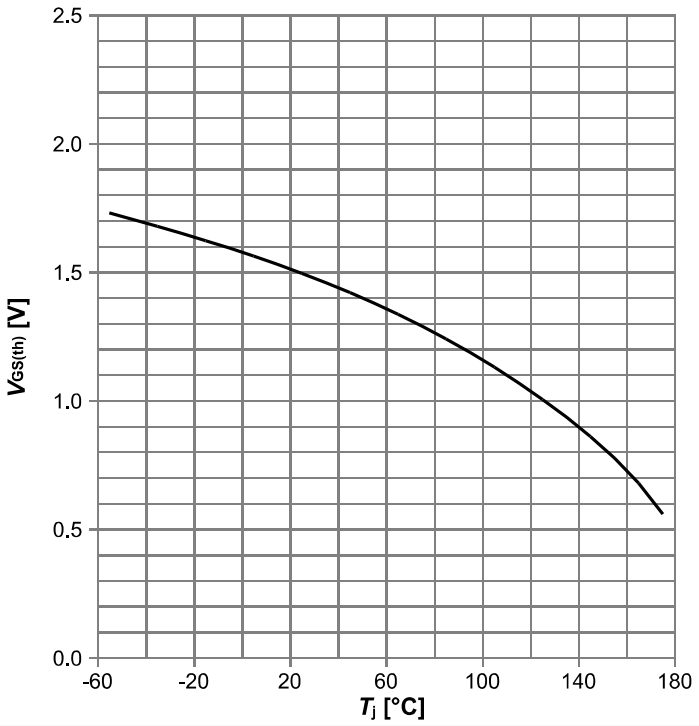
$g_{fs}=f(I_D)$; $T_j=25$ °C

Diagram 9: Drain-source on-state resistance



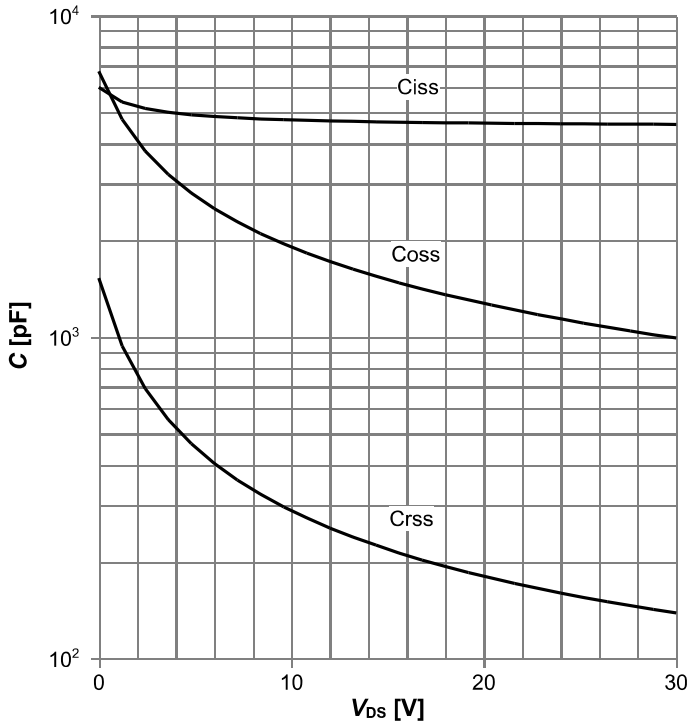
$R_{DS(on)}=f(T_j)$; I_D=30 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



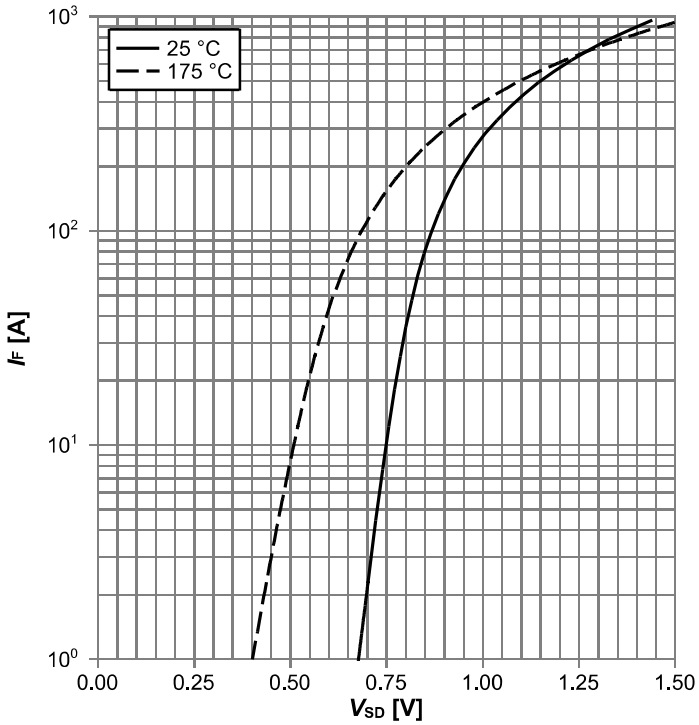
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$; I_D=250 µA

Diagram 11: Typ. capacitances



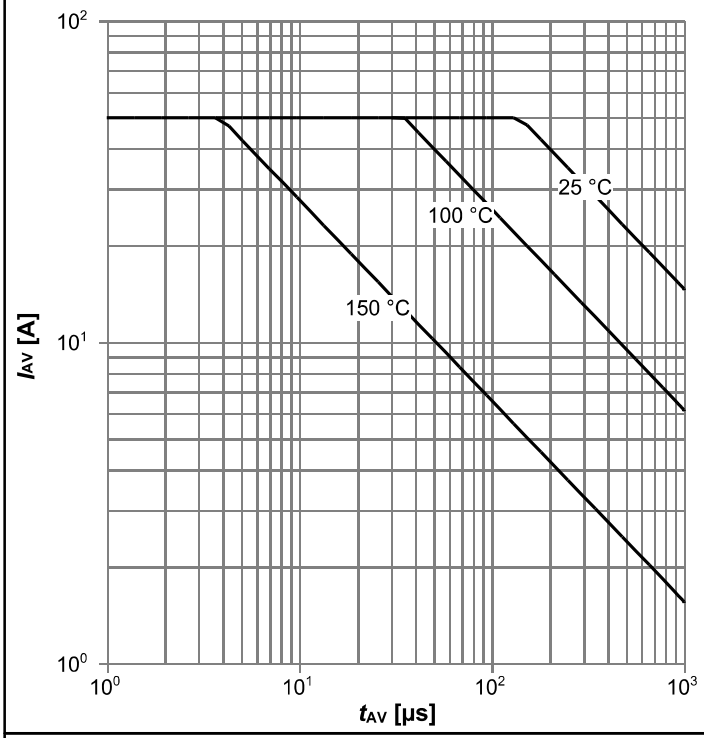
$C=f(V_{DS})$; V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



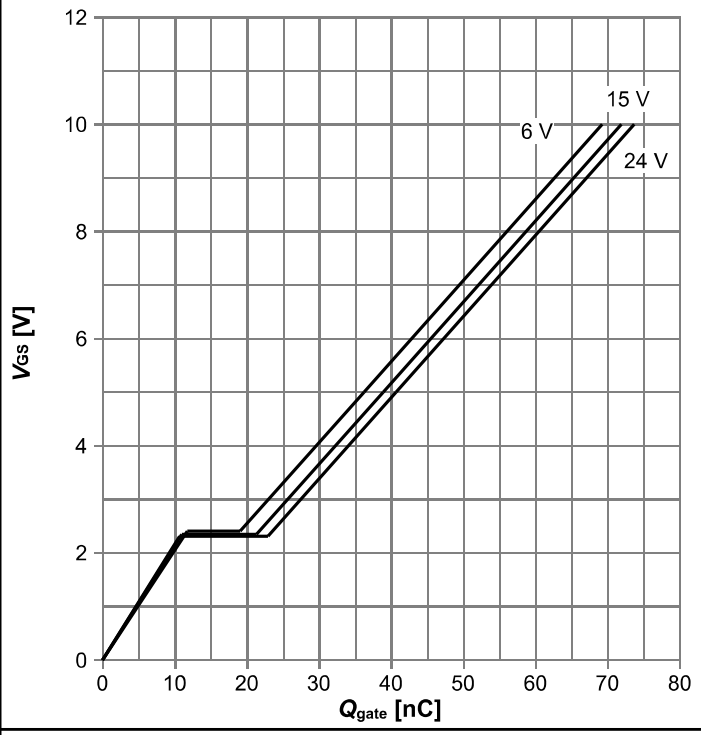
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



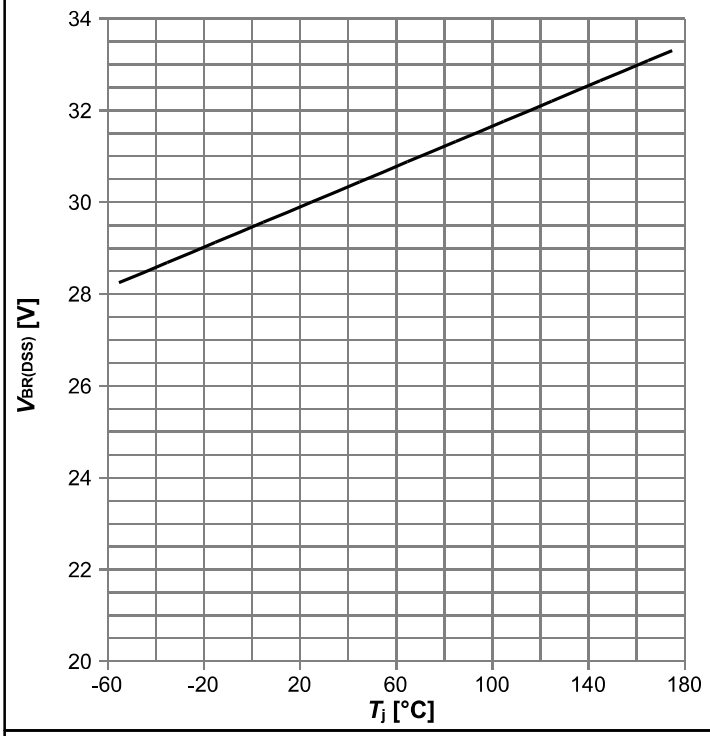
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



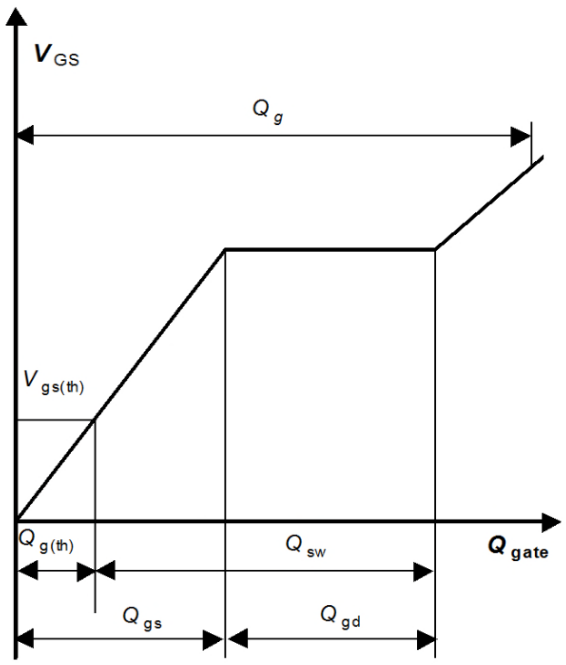
V_{GS}=f(Q_{gate}); I_D=30 A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

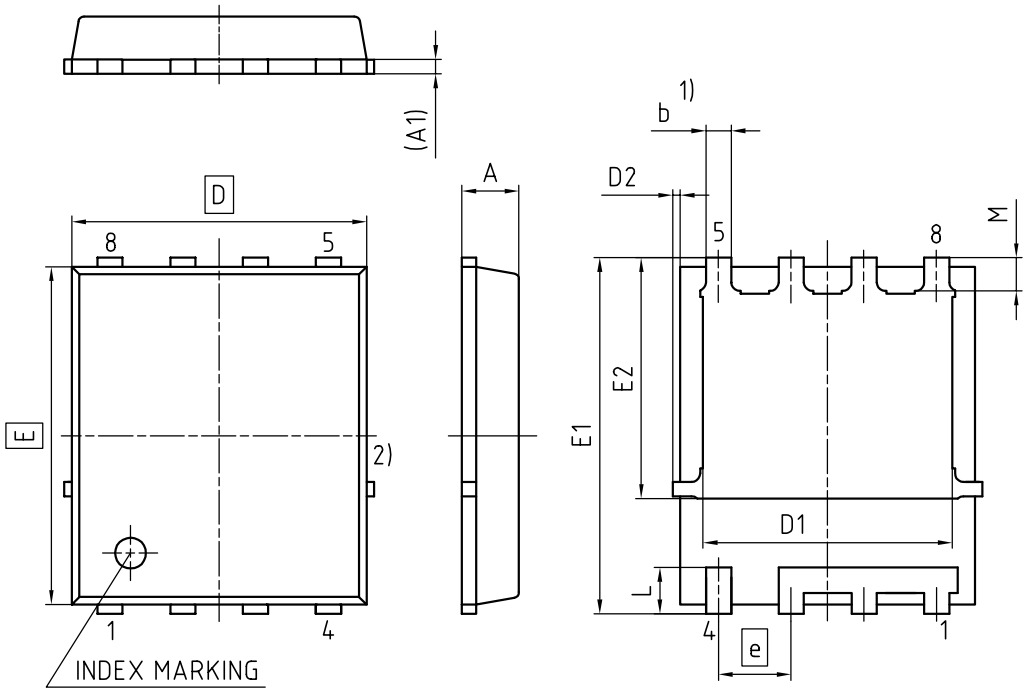


$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram Gate charge waveforms



5 Package Outlines



1) EXCLUDING MOLD FLASH
2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
LEAD LENGTH UP TO ANTI FLASH LINE
ALL METAL SURFACES ARE PLATED, EXCEPT AREA OF CUT

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
A1	0.15	0.35
b	0.26	0.54
D	4.80	5.35
D1	3.70	4.40
D2	0.02	0.23
E	5.70	6.10
E1	5.90	6.42
E2	3.88	4.42
e	1.27	
L	0.69	0.90
M	0.45	0.69

DOCUMENT NO.	Z8B000193699
REVISION	03
SCALE 10:1	0 1 2 3mm
EUROPEAN PROJECTION	
ISSUE DATE	19.06.2019

Figure 1 Outline PG-TDSON-8 FL, dimensions in mm

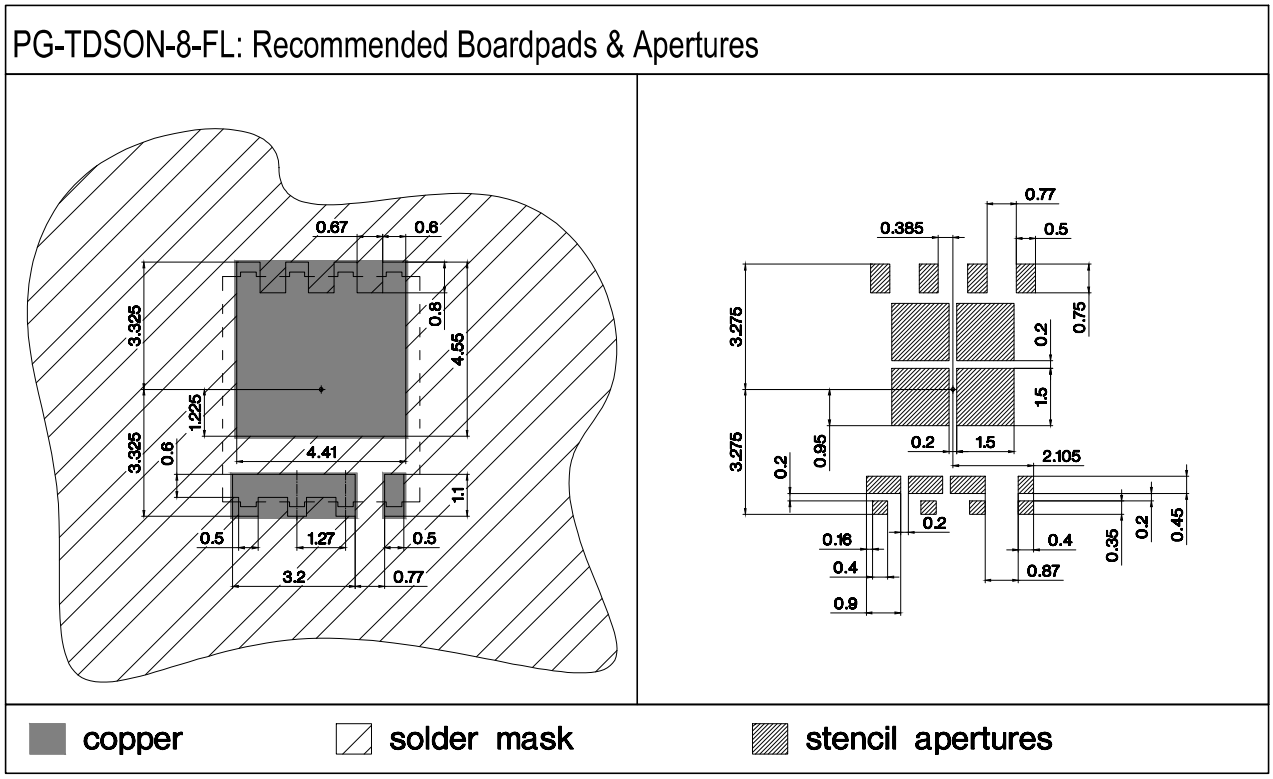


Figure 2 Outline Boardpads (TDSON-8 FL)

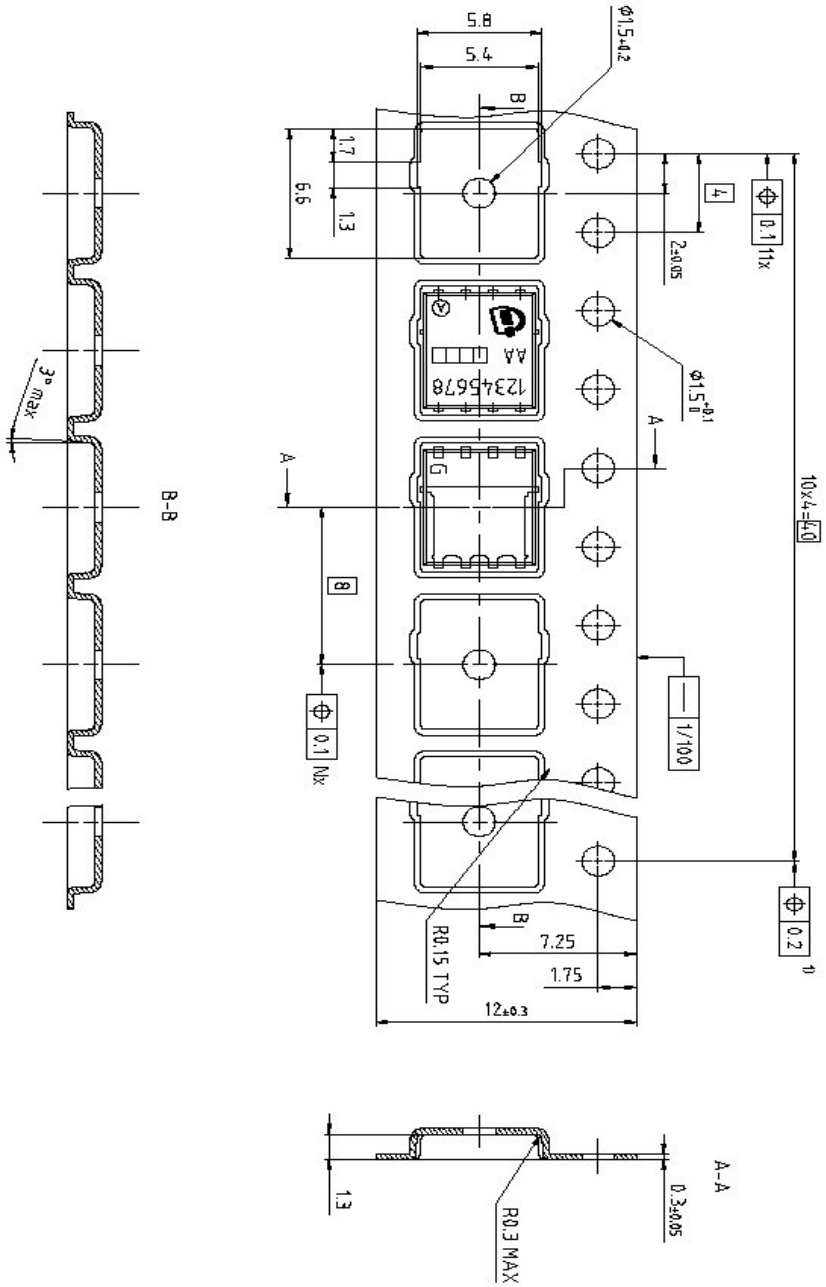


Figure 3 Outline Tape (TDSON-8 FL)

Revision History

BSC011N03LST

Revision: 2020-11-12, Rev. 2.3

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2017-03-01	Release of final version
2.1	2017-10-30	Insert footnote under Vgs
2.2	2019-10-01	Update package drawings
2.3	2020-11-12	Update current rating

Mouser Electronics

Authorized Distributor

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